

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	"20040217355"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 12:34
L2	3	"6876145"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 12:34
L3	8	"5932975"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 13:06
L4	1978098	display	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 13:06
L5	38279	4 & (plurality with pixel)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 13:07
L6	2690	5 & electroluminescent	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 13:11
L7	0	3 & (driv\$3 near5 transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 13:11
L8	0	2 & (driv\$3 near5 transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 13:12

L9	861	6 & (driv\$3 near5 transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 13:12
L10	76	6 & ((driv\$3 near5 transistor) with ((P near3 type) & drain\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 13:41
L11	388	(kiyoshi near2 yoneda).in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 13:16
L12	1	10 & 11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 13:17
L13	2	1 & (select\$3 with transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 13:18
L14	2	1 & (select\$3 same transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 13:18
L15	2	1 & (select\$3 & transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 13:25
L16	1	15 & (glass\$3 with substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 14:01

L17	43	10 & (glass\$3 with substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 13:27
L18	33	17 & (light\$3 with drain\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 13:35
L19	12	18 & ((p near3 type) with concentrat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 13:57
L20	12	17 & (light\$3 with doped\$3 with drain\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 13:36
L21	15	6 & ((driv\$3 near5 transistor) same ((P near3 type) & (light\$3 near12 dop\$3 near12 drain\$3)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 14:02
L22	12	21 & (glass\$3 with substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 13:56
L23	12	21 & ((p near3 type) same concentrat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 14:01
L24	2	"20040065902"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 13:59

L25	1	24 & ((p near3 type) same concentrat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 14:01
L26	1	24 & ((p near3 type) with concentrat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 14:01
L27	1	26 & (glass\$3 with substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 14:03
L28	0	27 & ((driv\$3 near5 transistor) same ((P near3 type) & (light\$3 near12 dop\$3 near12 drain\$3)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 14:05
L29	2	"20040089862"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 14:03
L30	0	29 & (glass\$3 & substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 14:05
L31	0	3 & ((driv\$3 near5 transistor) same ((P near3 type) & (light\$3 near12 dop\$3 near12 drain\$3)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 14:51
L32	0	3 & ((driv\$3 near5 transistor) & ((P near3 type) & (light\$3 near12 dop\$3 near12 drain\$3)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 14:05

L33	0	3 & (glass\$3 & substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 14:48
L34	316	(mutsumi near1 kimura).in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 14:47
L35	29	34 & (glass\$3 with substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 14:48
L36	8	35 & 6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 14:48
L37	0	36 & ((driv\$3 near5 transistor) same ((P near3 type) & (light\$3 near12 dop\$3 near12 drain\$3)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 14:52
L38	0	36 & ((driv\$3 near5 transistor) & ((P near3 type) & (light\$3 near12 dop\$3 near12 drain\$3)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 14:52
L39	3	34 & ((driv\$3 near5 transistor) & ((P near3 type) & (light\$3 near12 dop\$3 near12 drain\$3)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 14:59
L40	2	29 & concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 15:28

L41	2	29 & concentrat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 15:34
L42	1	41 & substrat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 15:44
L43	2	1 & (light\$3 near12 dop\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 15:46
L44	2	1 & ((region light\$3) with dop\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 15:47
L45	1	1 & ((p near3 type) with impurity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 15:48
L46	1	1 & ((p near3 type) with impurity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 15:49
L47	2	1 & (dop\$3 with drain)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 15:56
L48	2	1 & dop\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 16:03

L49	1	29 & (p near3 type)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 16:04
L50	1	29 & (impurity with region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 16:05
L51	1	50 & insulat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 16:21
L52	18	34 & (impurity with concentrat\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 16:24
L53	6	52 & boron	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 16:25
L54	5	53 & ((p near3 type) with (driv\$3 near5 (transistor tft)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 16:27
L55	5	54 & substrat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 16:31
L56	0	29 & transparent	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/29 16:32